Notice of Allowability	Application No.	Applicant(s)	
	10/050,078	OKUMURA, TOSHIYUKI	
	Examiner	Art Unit	
	Cornelius H. Jackson	2828	
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to	olication. If not included will be mailed in due cours	se. THIS
1. This communication is responsive to the Amendment filed	<u>18 April 2005</u> .		
2. The allowed claim(s) is/are 19,22-24,30,37-41 and 59.			
3. The drawings filed on 17 January 2002 and 18 April 2005	are accepted by the Examiner.		
<ul> <li>4. Acknowledgment is made of a claim for foreign priority unall a) All b) Some* c) None of the: <ol> <li>Certified copies of the priority documents have</li> <li>Certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> </ol> </li> <li>* Certified copies not received:</li> </ul>	been received. been received in Application No		om the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirer	nents
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			E OF
<ul> <li>6. CORRECTED DRAWINGS (as "replacement sheets") muse (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examiner's Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR 1)</li> </ul>	on's Patent Drawing Review (PTO-	ffice action of	c) of
each sheet. Replacement sheet(s) should be labeled as such in t	he header according to 37 CFR 1.121(c	1).	
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT			he
Attachment(s)  1. Notice of References Cited (PTO-892)	5. Notice of Informal P	atent Application (PTO-152	2)
2.   Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summary	•	
<ul> <li>3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date <u>2/16/05</u></li> <li>4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material</li> </ul>	<u> </u>		<b>:</b> e

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#### **DETAILED ACTION**

# Response to Arguments

1. Acknowledgment is made that applicant's Amendment, filed on 18 April 2005, has been entered. Upon entrance of the Amendment, claims 34-36, 42-58 and 60 were canceled. Claims 19, 22-24, 30, 37-41 and 59 are now pending in the current application.

### **Drawings**

2. The drawings were received on 18 April 2005. These drawings are accepted by the Examiner.

# Allowable Subject Matter

- 3. Claims 19, 22-24, 30, 37-41 and 59 are allowed.
- 4. The following is a statement of reasons for the indication of allowable subject matter:

Regarding claims 22-24, prior art fails to disclose, teach, or suggest, alone or in combination, a gallium nitride semiconductor device as claimed having cladding layer with a ridge surface and a planar surface and an active layer containing two to four quantum well layers and one to three barrier layers respectively, each interposed

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between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less.

Regarding claims 19 and 30, prior art fails to disclose, teach, or suggest, alone or in combination, a gallium nitride semiconductor device as claimed being a self-oscillating semiconductor laser device, **see specification**, **page 26**, **lines 3-10**, and having an active layer containing two to four quantum well layers and one to three barrier layers respectively, each interposed between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less.

Regarding claim 59, prior art fails to disclose, teach, or suggest, alone or in combination, a gallium nitride semiconductor device as claimed having a p-type cladding layer that forms at least part of a ridge structure and an active layer containing two to four quantum well layers and one to three barrier layers respectively, each interposed between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less.

# **Conclusion**

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Cornelius H. Jackson whose telephone number is (571)272-1942. The examiner can normally be reached on 8:00 - 5:00, Monday - Friday.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, MinSun Harvey can be reached on (571)272-1835. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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MINSUN OH HARVEY PRIMARY EXAMINER